

Docket: TSMC 00 - 299C  
S/N: TBD

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

From: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

Continuation Application Based upon Application  
Serial No.: 09/932,730, Filed: 08/20/01

Inventor: Chao-Chieh Tsai

Title: High  $f_{\text{MAX}}$  Deep Submicron MOSFET

Group Art Unit: TBD Examiner: TBD  
Attorney Docket: TSMC 00 - 299C


**PRELIMINARY AMENDMENT**

Dear Sir:

As a Preliminary Amendment for the above-identified  
Continuation Application filed concurrently herewith, please consider the  
following remarks.

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with  
the United States Postal Service as first class mail in an envelope addressed to:  
Commissioner of Patent and Trademarks, Washington, D.C. 20231, on  
July 21, 2003.

Signature/Date  July 21, 2003

Stephen B. Ackerman  
Reg. No. 37,761

July 18, 2003

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile     Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

**Continuation of**  
Serial No.: 09/932,730 8/20/01  
  
CHAO-CHIEH TSAI, SHYH-CHYI WONG,  
CHUNG-LONG CHANG  
  
HIGH  $F_{MAX}$  DEEP SUBMICRON MOSFET

**PRELIMINARY AMENDMENT**

Dear Sir:


This is a preliminary amendment for the above referenced Continuation. Please amend the above identified application for patent as follows:

**CERTIFICATE OF MAILING**

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Stephen B. Ackerman, Reg. No. 37,761

Signature/Date

 7/21/03